

L Number	Hits	Search Text	DB	Time stamp
1	80	((((N ADJ1 type) near4 ((photo adj1 (sens\$3 or diode)) or sensor or diode)) same ((P ADJ1 type) near4 transistor\$1)) and @ad<=19990826) and (cmos or mos of mosfet) ("4258684").PN.	USPAT; US-PGPUB	2004/01/11 14:21
2	1	("4258684").PN.	USPAT; US-PGPUB	2004/01/11 11:17
3	1	("4528684").PN.	USPAT; US-PGPUB	2004/01/11 11:53
4	2	((("5781233") or ("5818052"))).PN.	USPAT; US-PGPUB	2004/01/11 12:01
5	12	5818052.URPN.	USPAT	2004/01/11 11:55
6	1	5818052.PN.	USPAT; US-PGPUB	2004/01/11 12:01
7	1	"27" AND 5818052.PN.	USPAT; US-PGPUB	2004/01/11 12:02
8	1	"53" AND 5818052.PN.	USPAT; US-PGPUB	2004/01/11 12:03
9	1	(mos OR mosfet) AND 5818052.PN.	USPAT; US-PGPUB	2004/01/11 12:04
10	5730	guard with ring\$1	USPAT; US-PGPUB	2004/01/11 12:05
11	551	(P ADJ1 type) with (guard with ring\$1)	USPAT; US-PGPUB	2004/01/11 12:05
12	41066	(P ADJ1 type) with substrate\$1	USPAT; US-PGPUB	2004/01/11 14:20
13	248	((P ADJ1 type) with (guard with ring\$1)) same ((P ADJ1 type) with substrate\$1)	USPAT; US-PGPUB	2004/01/11 12:05
14	10416	(N ADJ1 type) near4 well\$1	USPAT; US-PGPUB	2004/01/11 12:06
15	38	((((P ADJ1 type) with (guard with ring\$1)) same ((P ADJ1 type) with substrate\$1)) same ((N ADJ1 type) near4 well\$1)	USPAT; US-PGPUB	2004/01/11 12:06
16	24	((((P ADJ1 type) with (guard with ring\$1)) same ((P ADJ1 type) with substrate\$1)) same ((N ADJ1 type) near4 well\$1)) and @ad<=19990826	USPAT; US-PGPUB	2004/01/11 14:24
17	34763	APS	USPAT; US-PGPUB	2004/01/11 14:20
18	14324	(P ADJ1 type) NEAR5 transistor	USPAT; US-PGPUB	2004/01/11 14:24
19	3401	(N adj1 type) near5 (diode or (photo adj1 diode))	USPAT; US-PGPUB	2004/01/11 14:21
20	716	((P ADJ1 type) NEAR5 transistor) and ((N adj1 type) near5 (diode or (photo adj1 diode)))	USPAT; US-PGPUB	2004/01/11 14:21
21	250	((P ADJ1 type) NEAR5 transistor) same ((N adj1 type) near5 (diode or (photo adj1 diode)))	USPAT; US-PGPUB	2004/01/11 14:21
22	2	APS and (((P ADJ1 type) NEAR5 transistor) same ((N adj1 type) near5 (diode or (photo adj1 diode))))	USPAT; US-PGPUB	2004/01/11 14:22
23	160	((((P ADJ1 type) NEAR5 transistor) same ((N adj1 type) near5 (diode or (photo adj1 diode)))) and @ad<=19990826	USPAT; US-PGPUB	2004/01/11 14:50
24	83	(P ADJ1 type) NEAR5 reset near5 transistor	USPAT; US-PGPUB	2004/01/11 14:45
25	3	((P ADJ1 type) NEAR5 reset near5 transistor) same ((N adj1 type) near5 (diode or (photo adj1 diode)))	USPAT; US-PGPUB	2004/01/11 14:45
26	1	5757008.pn.	USPAT; US-PGPUB	2004/01/11 14:45
27	41065	(P ADJ1 type) with substrate	USPAT; US-PGPUB	2004/01/11 14:45
28	1	5757008.pn. and ((P ADJ1 type) with substrate)	USPAT; US-PGPUB	2004/01/11 14:47

29	305	schottky with ((N adj1 type) near5 (diode or (photo adj1 diode)))	USPAT; US-PGPUB	2004/01/11 14:50
30	1	((P ADJ1 type) with substrate) and (5757008.pn. and ((P ADJ1 type) with substrate))	USPAT; US-PGPUB	2004/01/11 14:50
31	994	((N adj1 type) near5 (diode or (photo adj1 diode))) same ((P ADJ1 type) with substrate)	USPAT; US-PGPUB	2004/01/11 14:50
32	107	schottky and ((N adj1 type) near5 (diode or (photo adj1 diode))) same ((P ADJ1 type) with substrate)	USPAT; US-PGPUB	2004/01/11 14:50
33	77	(schottky and ((N adj1 type) near5 (diode or (photo adj1 diode))) same ((P ADJ1 type) with substrate))) and @ad<=19990826	USPAT; US-PGPUB	2004/01/11 15:45
34	17	imag\$3 and ((schottky and ((N adj1 type) near5 (diode or (photo adj1 diode))) same ((P ADJ1 type) with substrate))) and @ad<=19990826)	USPAT; US-PGPUB	2004/01/11 15:11
35	0	mosfet and 5757008.pn.	USPAT; US-PGPUB	2004/01/11 15:16
36	5476	column with (read adj1 out)	USPAT; US-PGPUB	2004/01/11 15:16
37	0	5757008.pn. and (column with (read adj1 out))	USPAT; US-PGPUB	2004/01/11 15:43
38	1	(ground near5 voltage) and 5757008.pn.	USPAT; US-PGPUB	2004/01/11 15:45
39	79	(ground near5 voltage) same (guard with ring\$1)	USPAT; US-PGPUB	2004/01/11 15:45
40	46	((ground near5 voltage) same (guard with ring\$1)) and @ad<=19990826	USPAT; US-PGPUB	2004/01/11 15:46
41	1	((N adj1 type) near5 (diode or (photo adj1 diode))) and ((ground near5 voltage) same (guard with ring\$1)) and @ad<=19990826)	USPAT; US-PGPUB	2004/01/11 15:53
42	0	((N adj1 type) near5 (diode or (photo adj1 diode))) same voltage same crosstalk	USPAT; US-PGPUB	2004/01/11 15:53
43	3	((N adj1 type) near5 (diode or (photo adj1 diode))) same crosstalk	USPAT; US-PGPUB	2004/01/11 16:44
44	7	(("5372955") or ("5757008") or ("5818052") or ("5881184") or ("6049111") or ("6175383") or ("6252218")).PN.	USPAT; US-PGPUB	2004/01/11 16:44
-	2	"6362767"	USPAT; US-PGPUB	2004/01/10 15:46
-	1	5283428.pn.	USPAT; US-PGPUB	2004/01/10 15:26
-	3	(("5953060") or ("5933190") or ("6011251")).PN.	USPAT; US-PGPUB	2004/01/10 18:09
-	3193	(N ADJ1 type) near4 ((photo adj1 (sens\$3 or diode)) or sensor or diode)	USPAT; US-PGPUB	2004/01/11 12:06
-	13051	(P ADJ1 type) near4 transistor\$1	USPAT; US-PGPUB	2004/01/11 12:05
-	195	((N ADJ1 type) near4 ((photo adj1 (sens\$3 or diode)) or sensor or diode)) same ((P ADJ1 type) near4 transistor\$1)	USPAT; US-PGPUB	2004/01/10 18:12
-	117	((N ADJ1 type) near4 ((photo adj1 (sens\$3 or diode)) or sensor or diode)) same ((P ADJ1 type) near4 transistor\$1)) and @ad<=19990826	USPAT; US-PGPUB	2004/01/10 18:12
-	416800	cmos or mos of mosfet	USPAT; US-PGPUB	2004/01/10 18:13
-	186	((N ADJ1 type) near4 ((photo adj1 (sens\$3 or diode)) or sensor or diode)) with (CMOS or MOS)	USPAT; US-PGPUB	2004/01/10 18:13
-	414	((P ADJ1 type) near4 transistor\$1) with MOSFET	USPAT; US-PGPUB	2004/01/10 18:13

-	0	((N ADJ1 type) near4 ((photo adj1 (sens\$3 or diode)) or sensor or diode)) with (CMOS or MOS)) same ((P ADJ1 type) near4 transistor\$1) with MOSFET)	USPAT; US-PGPUB	2004/01/10 18:13
-	41065	(P ADJ1 type) with substrate	USPAT; US-PGPUB	2004/01/10 18:14
-	48	(((((N ADJ1 type) near4 ((photo adj1 (sens\$3 or diode)) or sensor or diode)) same ((P ADJ1 type) near4 transistor\$1)) and @ad<=19990826) and (cmos or mos of mosfet)) and ((P ADJ1 type) with substrate)	USPAT; US-PGPUB	2004/01/11 11:17
-	9	imag\$3 and ((((((N ADJ1 type) near4 ((photo adj1 (sens\$3 or diode)) or sensor or diode)) same ((P ADJ1 type) near4 transistor\$1)) and @ad<=19990826) and (cmos or mos of mosfet)) and ((P ADJ1 type) with substrate))	USPAT; US-PGPUB	2004/01/10 18:32